

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2SK367

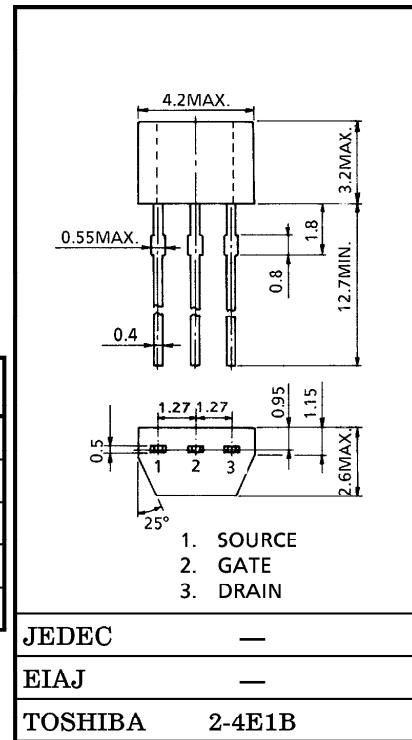
FOR AUDIO, HIGH VOLTAGE AMPLIFIER AND CONSTANT CURRENT APPLICATIONS

Unit in mm

- High Breakdown Voltage : $V_{GDS} = -100V$ (Min.)
- High Input Impedance : $I_{GSS} = -1.0nA$ (Max.) ($V_{GS} = -80V$)
- Small Package

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-drain Voltage	V_{GDS}	-100	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	200	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~125	$^\circ C$



JEDEC	—
EIAJ	—
TOSHIBA	2-4E1B

Weight : 0.13g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I_{GSS}	$V_{GS} = -80V, V_{DS} = 0$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS} = 0, I_G = -100\mu A$	-100	—	—	V
Drain Current	I_{DSS} (Note)	$V_{DS} = 10V, V_{GS} = 0$	0.6	—	6.5	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 10V, I_D = 0.1\mu A$	-0.4	—	-3.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	1.5	4.6	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	13	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V, I_D = 0, f = 1MHz$	—	3	—	pF
Noise Figure	NF	$V_{DS} = 10V, V_{GS} = 0, R_G = 100k\Omega, f = 100Hz$	—	0.5	—	dB

Note : I_{DSS} Classification O : 0.6~1.4mA, Y : 1.2~3.0mA, GR : 2.6~6.5mA

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